

CMPDM7003

**SURFACE MOUNT
N-CHANNEL
ENHANCEMENT-MODE
SILICON MOSFET**



SOT-23 CASE

APPLICATIONS:

- Load/Power switches
- Power supply converter circuits
- Battery powered portable equipment

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Drain-Source Voltage
Drain-Gate Voltage
Gate-Source Voltage
Continuous Drain Current
Maximum Pulsed Drain Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPDM7003 is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers low $r_{DS(ON)}$ and ESD protection up to 2kV.

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FEATURES:

- ESD protection up to 2kV
- Low $r_{DS(ON)}$
- Low $V_{DS(ON)}$
- Low threshold voltage
- Fast switching
- Logic level compatibility

SYMBOL

V_{DS}	50	V
V_{DG}	50	V
V_{GS}	12	V
I_D	280	mA
I_{DM}	1.5	A
P_D	350	mW
T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Θ_{JA}	357	$^{\circ}\text{C/W}$

UNITS

ELECTRICAL CHARACTERISTICS: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=5.0\text{V}$			100	nA
I_{GSSF}, I_{GSSR}	$V_{GS}=10\text{V}$			2.0	μA
I_{GSSF}, I_{GSSR}	$V_{GS}=12\text{V}$			2.0	μA
I_{DSS}	$V_{DS}=50\text{V}, V_{GS}=0$			50	nA
BV_{DSS}	$V_{GS}=0, I_D=10\mu\text{A}$	50			V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.49		1.0	V
V_{SD}	$V_{GS}=0, I_S=115\text{mA}$			1.4	V
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=50\text{mA}$		1.6	3.0	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=50\text{mA}$		1.3	2.5	Ω
$r_{DS(ON)}$	$V_{GS}=5.0\text{V}, I_D=50\text{mA}$		1.1	2.0	Ω
g_{FS}	$V_{DS}=10\text{V}, I_D=200\text{mA}$	200			mS
C_{rss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			5.0	pF
C_{iss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			50	pF
C_{oss}	$V_{DS}=25\text{V}, V_{GS}=0, f=1.0\text{MHz}$			25	pF

R1 (27-January 2010)

CMPDM7003

SURFACE MOUNT

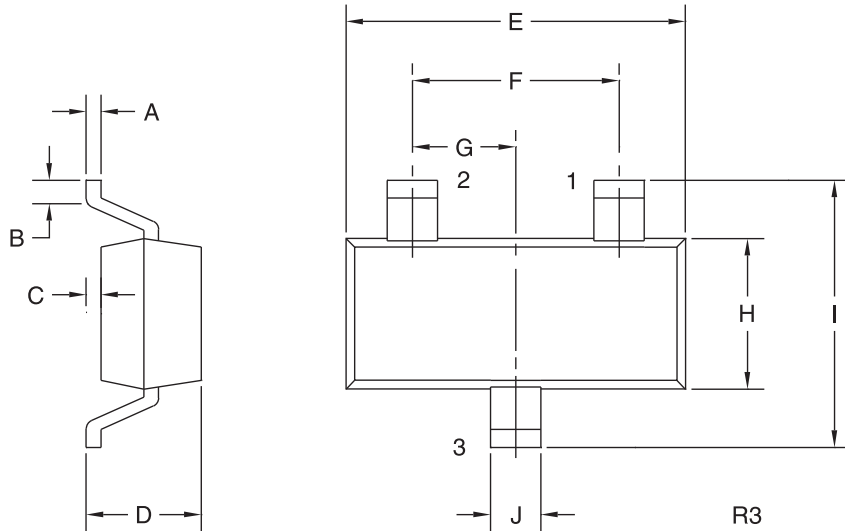
N-CHANNEL

ENHANCEMENT-MODE

SILICON MOSFET



SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Gate
- 2) Source
- 3) Drain

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DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R1 (27-January 2010)

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